# MSKSEMI 美森科













**ESD** 

TV

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MCP6001UT-I/\*\*(MS)

**Product specification** 





#### **GENERAL DESCRIPTION**

The MCP6001UT-I/\*\*(MS)is a CMOS operational amplifier that uses the proprietary auto-calibration technique to simultaneously provide very low offset voltage,near-zero drift over time and temperature. This miniature, high-precision, low quiescent current amplifiers offer high-impedance inputs that have a common-mode range 200mV beyond the rails, and rai-to-rail output that swings within 50mV of the rails, single or dual supplies as low as  $2.1V(\pm 1.35V)$  and up to  $5.5V(\pm 2.75V)$  can be used. This device is optimized for low voltage, single supply operation.

The MCP6001UT-I/\*\*(MS)offers excellent CMRR without the crossover associated with traditional complementary input stages. This design results in superior performance for driving analog-to-digital converters (ADC) without degradation of differential linearity.

The MCP6001UT-I/\*\*(MS)is available in the 5-pin SOT-23-5 and SC70-5 packages, and specified for operation from -55  $^{\circ}$ C to 125  $^{\circ}$ C.

#### **FEATURES**

- VDD range:2.1V to 5.5V
- Low Ofset Voltage:0.5mV (Typical)
- Low Drift:0.65µV/C(Typical)
- Low Noise
- Quiescent Current:28µA
- Rail to Rail Input/Output
- MicroSize Packages:SC70-5 and SOT23-5

# **Applications**

- Transducers
- ●Temperature Measurement
- Electronic Scales
- Medical instrumentation
- Handheld Test Equipment

#### **Reference News**

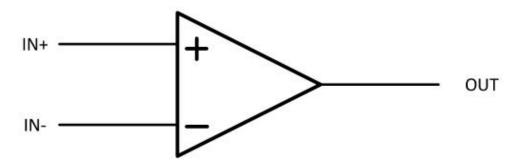
PACKAGE OUTLINE		PIN CONFIGURATION	Marking		
		IN+ 1 5 VDD	AF**	AF**	
SOT-23-5	SC70-5	SOT-23-5/SC70-5	SOT-23-5	SC70-5	

#### PIN DESCRIPTION

Pin Name	Pin Numbel	Description	
1 I N+	1	Noninverting inpu	
GND	2	Negative(lowest)power supply	
1IN-	3	Inverting inpu	
OUT	4	Output	
Vcc+	5	Positive (highest) power supply	



# **SIMPLIFIED SCHEMATIC**



**Figure 1.Simpliied Schematic** 

### **ABSOLUTE MAXIMUM RATINGS**

Thermal Resistance 0 Jc	130°C/W
Supply Voltage	2.1to 5.5V
Signal Input Terminals Voltage0.1 t	o (V+)+0.1V
Operating Junction Temperature	150°C
Operating Temperature Range	25°C to 85°C
Storage Temperature	-65°℃ to 150℃



#### **ELECTRICAL CHARACTERISTICS**

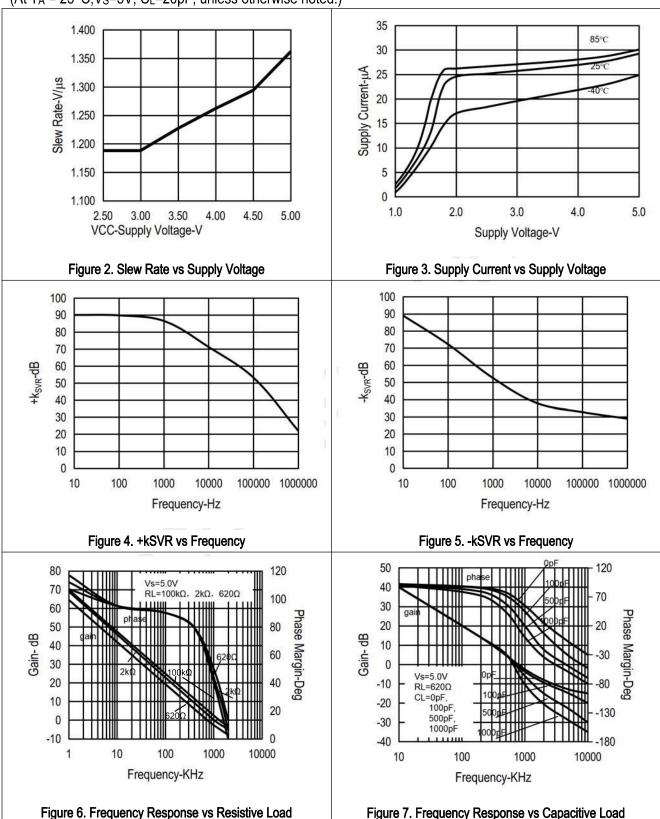
(At TA= $25^{\circ}$  C, RL=10k connected to Vs/2, and Vour=Vs/2, unless otherwise noted.)

PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
Input Offset Voltage	Vs=±2.5V	-3	0. 5	3	mV
nput Offset Voltage Drift	TA=-55° ℃ to 125° ℃		0. 65		μV/°C
Power Supply Rejection Ratio	Vs =2.1V to 5.5V TA=-55℃ to 125℃	80	90		dB
Input Bias Curren	TA=25℃		2. 0		pA
Input Offset Current			1.0		pА
Common-mode Voltage Range		(V-)-0.1		(V+)+0.1	V
Common-mode Rejection Ratio	V-)-0.1 <vcm<(v+)+0.1 TA=-55°C to 125°C</vcm<(v+)+0.1 	80	95		dB
Open Loop Voltage Gain	(V-)+100mV <vo<(v+)-10 0mV, RL=10k TA=-55° ℃ to 125℃</vo<(v+)-10 	80	100		dB
Gain-bandwidth product	CL=120pF		1.5		MHz
Slew Rate	G=+1		1.2		V/μs
Specified Voltage Range		1.8		5. 5	V
Quiescent Current			28	40	μА
Operating Temperature Range		-25		85	$^{\circ}$
Storage Temperature Range		-65		150	°C



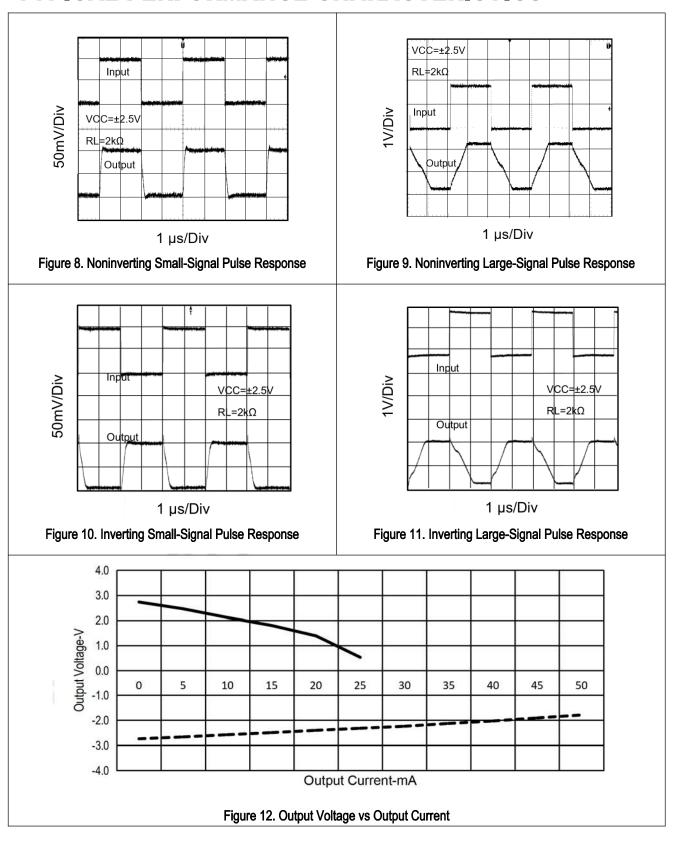
# **TYPICAL PERFORMANCE CHARACTERISTICS**

(At T<sub>A</sub> = 25°C,V<sub>S</sub>=5V, C<sub>L</sub>=20pF, unless otherwise noted.)





## **TYPICAL PERFORMANCE CHARACTERISTICS**





# FUNCTIONAL DESCRIPTION Operating Voltage

The MCP6001UT-I/\*\*(MS)devices are fully specified and ensured for operation from 2.1V to 5.5 V.In addition,many specifications apply from -55℃to 125℃. Parameters that vary significantly with operating voltages or temperature are shown in the Typical Characteristics graphs.

#### **Unity-Gain Bandwidth**

The unity-gain bandwidth is the frequency up to which an amplifier with a unity gain may be operated without greatly distorting the signal. The MCP6001UT-I/\*\*(MS)device has a 1.5-MHz unity-gain bandwidth.

#### **APPLICATIONS INFORMATION**

The MCP6001UT-I/\*\*(MS)is a unity-gain stable,precision operational amplifier with very low offset voltage drift; these devices are also free from output phase reversal. Applications with noisy or high-impedance power supplies require decoupling capacitors close to the device power-supply pins. In most cases, 0.1 µF capacitors are adequate.

#### **Typical Application**

Figure 13 shows a simple circuit to convert a single-ended input into differential output. The MCP6001UT-I/\*\*(MS) could be used to build this circuit. The circuit is composed of two amplifiers. One amplifier acts as a buffer and creates a voltage, VouT+. The second amplifier inverts the input and adds a reference voltage to generate Vour-. Both Vour+ and Vour-range from 0.5 to 2 V. The difference, VDIFF, is the difference between Vour+ and VouT-.

#### Slew Rate

The slew rate is the rate at which an operational amplifier can change its output when there is a change on the input. The MCP6001UT-I/\*\*(MS)devices have a1 .2-V/µ s slew rate. The MCP6001UT-I/\*\*(MS)is characterized toperform with this technique; the recommended resistor value is approximately 20 k.

#### **Device Functional Modes**

The MCP6001UT-I/\*\*(MS)device has a single functional mode. The device is powered on as long as the power supply voltage is between 2.1V(±1.35V)and 5.5V(±2.75V)

#### **Detailed Design Procedure**

Linearity over the input range is key for good dc accuracy. The common mode input range and the output swing limitations determine the linearity. In general, an amplifier with rail-to-rail input and output swing is required. Bandwidth is a key concern for this design. Because MCP6001UT-I/\*\*(MS) has a bandwidth of 1MHz, this circuit will only be able to process signals with frequencies of less than 1 MHz.

Because the transfer function of Vour-is heavily reliant on resistors(R1,R2,R3,and R4),use resistors with low tolerances to maximize performance and minimize error. This design used resistors with resistance values of 36 k with tolerances measured to be within 2%. If the noise of the system is a key parameter, the user can select smaller resistance values (6 k or lower) to keep the overall system noise low. This ensures that the noise from the resistors is lower than the amplifier noise.



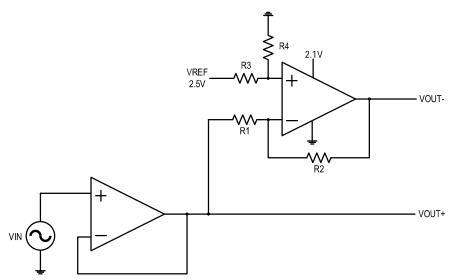
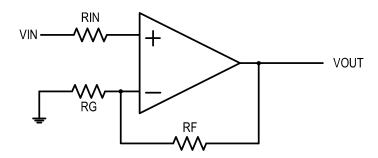


Figure 13. Schematic for Single-Ended Input to Differential Output Conversion

#### **LAYOUT**

Use good PCB layout practices for best operational performance of the device, including:

- Keep the length of input traces as short as possible.
- Run the input traces as far away from the supply lines as possible to reduce parasitic coupling.
- Place components close to device and to each other to reduce parasitic capacitance and parasitic errors.
- Use low-ESR, ceramic bypass capacitors to reduce the coupled noise by providing low impedance powe sources local to the analog circuitry.
- Grounding for analog and digital portions of circuitry separately to suppresse the noise.





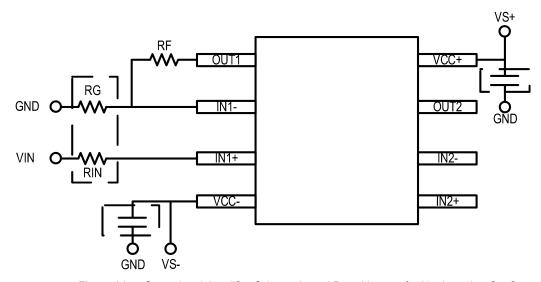
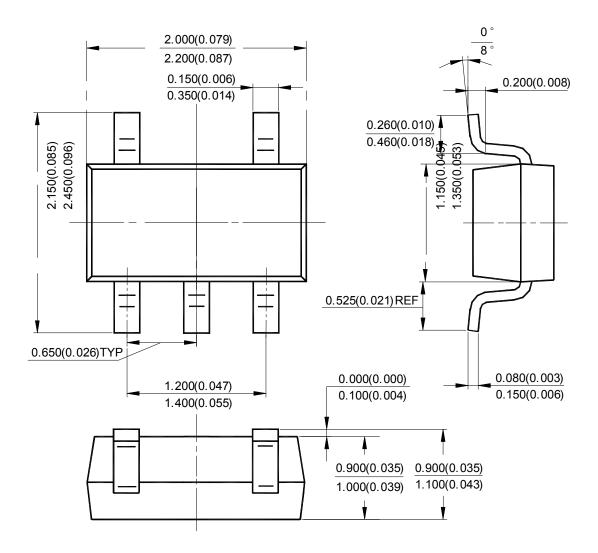


Figure 14. Operational Amplifier Schematic and Board Layout for Noninverting Configuration



# Package Outline Dimensions (All dimensions in mm(inch).)

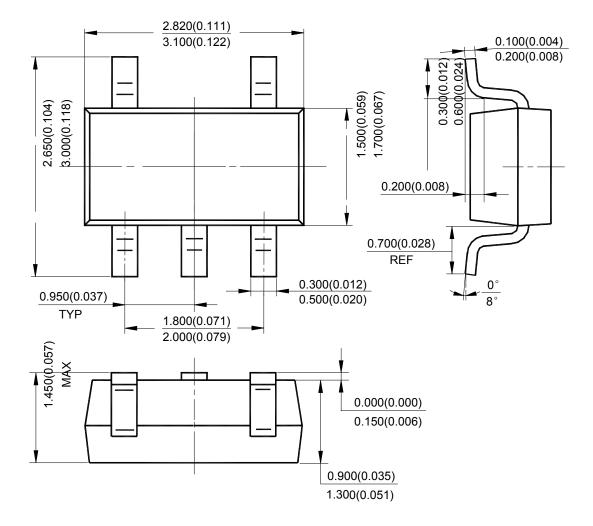
#### SC-70-5





#### Package Outline Dimensions (Cont. All dimensions in mm(inch).)

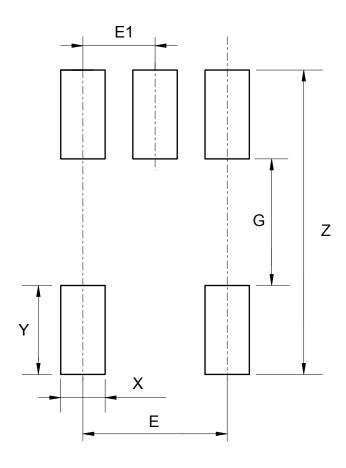
#### SOT-23-5





# **Suggested Pad Layout**

SC-70-5

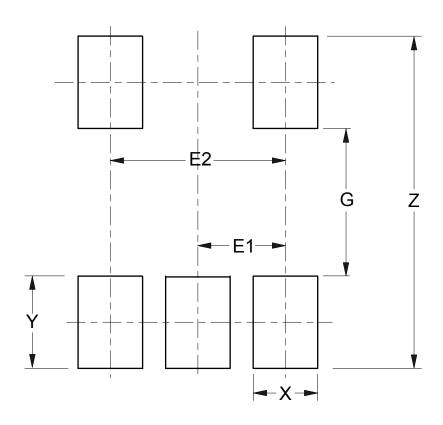


Dimongions	Z	G	X	Y	E	E1
Dimensions	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)
Value	2.740/0.108	1.140/0.045	0.400/0.016	0.800/0.031	1.300/0.051	0.650/0.026



# Suggested Pad Layout (Cont.)

SOT-23-5



Dimensions	Z	G	X	Y	E1	E2
Difficusions	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)
Value	3.600/0.142	1.600/0.063	0.700/0.028	1.000/0.039	0.950/0.037	1.900/0.075



# **REEL SPECIFICATION**

P/N	PKG	QTY
MCP6001UT-I/OT(MS)	SOT-23-5	3000
MCP6001UT-I/LT(MS)	SC70-5	3000



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